

MA700, MA700A

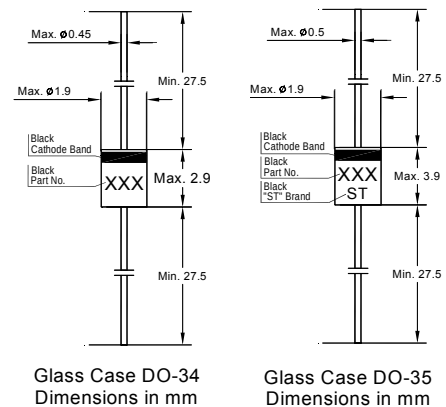
Silicon Epitaxial Planar Schottky Barrier Diodes

for ordinary wave detection

for super high speed switching

Features

- Low forward voltage and good wave detection efficiency
- Low reverse current



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	15	V
		30	
Reverse Voltage	V_R	15	V
		30	
Forward Current	I_F	30	mA
Peak Forward Current	I_{FM}	150	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 30\text{ mA}$	V_F	-	0.4	V
		-	1	
Reverse Current at $V_R = 15\text{ V}$ at $V_R = 30\text{ V}$	I_R	-	600	nA
		-	600	
Terminal Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_T	1.3	-	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{rr} = 1\text{ mA}$, $R_L = 100\ \Omega$	t_{rr}	1	-	ns
Detection Efficiency at $V_{in} = 3\text{ V}_{(peak)}$, $f = 30\text{ MHz}$, $R_L = 3.9\text{ K}\Omega$, $C_L = 10\text{ pF}$	η	60	-	%

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